NJT4030P, NJV4030PT1G, NJV4030PT3G

Bipolar Power Transistors

PNP Silicon

Features

- Epoxy Meets UL 94, V−0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CB}	40	Vdc
Emitter−Base Voltage	V_{EB}	6.0	Vdc
Base Current − Continuous	I_B	1.0	Adc
Collector Current − Continuous	I_C	3.0	Adc
Collector Current − Peak	I_{CM}	5.0	Adc
ESD − Human Body Model	HBM	3B	V
ESD − Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P_D @ T_A = 25°C (Note 1) Total P_D @ T_A = 25°C (Note 2)	P_D	 2.0 0.80	W
Thermal Resistance, Junction−to−Case Junction−to−Ambient (Note 1) Junction−to−Ambient (Note 2)	 $R_{\theta JA}$ $R_{\theta JA}$	 64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR−4 bd material.
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR−4 bd material.

ON Semiconductor®

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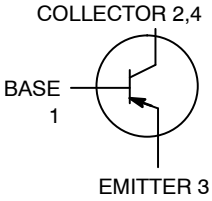
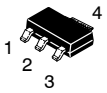
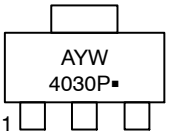
PNP TRANSISTOR
3.0 AMPERES
40 VOLTS, 2.0 WATTS





SOT−223
CASE 318E
STYLE 1

MARKING DIAGRAM



A	= Assembly Location
Y	Year
W	= Work Week
4030P	= Specific Device Code
▪	= Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NJT4030NT1G	SOT−223 (Pb−Free)	1000 / Tape & Reel
NJV4030NT1G		
NJT4030NT3G	SOT−223 (Pb−Free)	4000 / Tape & Reel
NJV4030NT3G		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Sustaining Voltage (I_C = 10 mAdc, I_B = 0 Adc)	$V_{CEO(sus)}$	40	–	–	Vdc
Emitter−Base Voltage (I_E = 50 μAdc, I_C = 0 Adc)	V_{EBO}	6.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc)	I_{CBO}	–	–	100	nAdc
Emitter Cutoff Current (V_{BE} = 6.0 Vdc)	I_{EBO}	–	–	100	nAdc
ON CHARACTERISTICS (Note 3)					
Collector−Emitter Saturation Voltage (I_C = 0.5 Adc, I_B = 5.0 mAdc) (I_C = 1.0 Adc, I_B = 10 mAdc) (I_C = 3.0 Adc, I_B = 0.3 Adc)	$V_{CE(sat)}$	 – – –	 – – –	 0.150 0.200 0.500	Vdc
Base−Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{BE(sat)}$	–	–	1.0	Vdc
Base−Emitter On Voltage (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	–	–	1.0	Vdc
DC Current Gain (I_C = 0.5 Adc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc) (I_C = 3.0 Adc, V_{CE} = 1.0 Vdc)	h_{FE}	 220 200 100	 – – –	 – 400 –	–
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 10 Vdc, f = 1.0 MHz)	C_{ob}	–	40	–	pF
Input Capacitance (V_{EB} = 5.0 Vdc, f = 1.0 MHz)	C_{ib}	–	130	–	pF
Current−Gain − Bandwidth Product (Note 4) (I_C = 500 mA, V_{CE} = 10 V, F_{test} = 1.0 MHz)	f_T	–	160	–	MHz

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. $f_T = |h_{FE}| \bullet f_{test}$

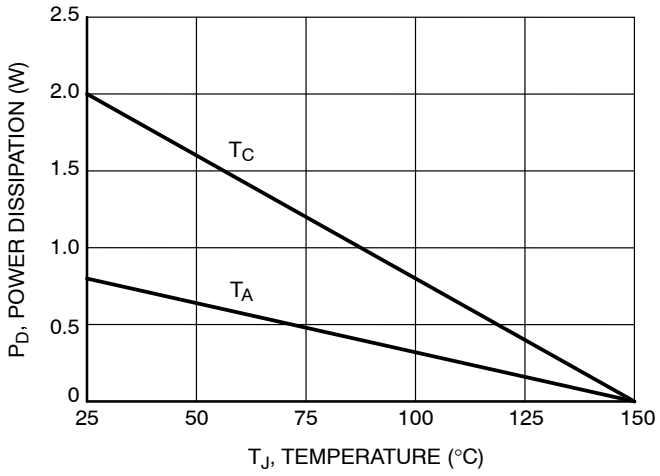


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

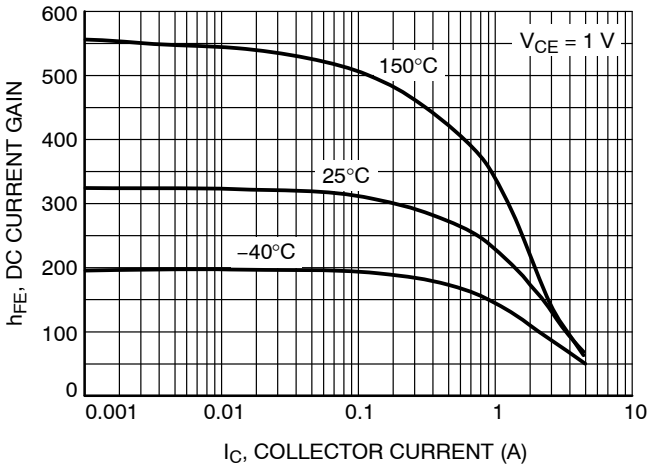


Figure 2. DC Current Gain

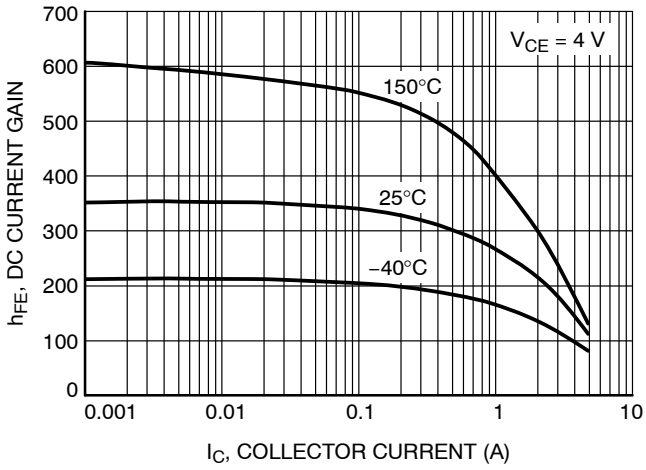


Figure 3. DC Current Gain

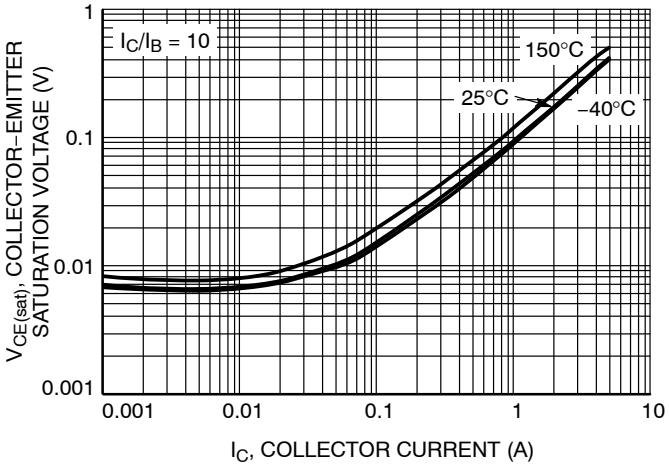


Figure 4. Collector−Emitter Saturation Voltage

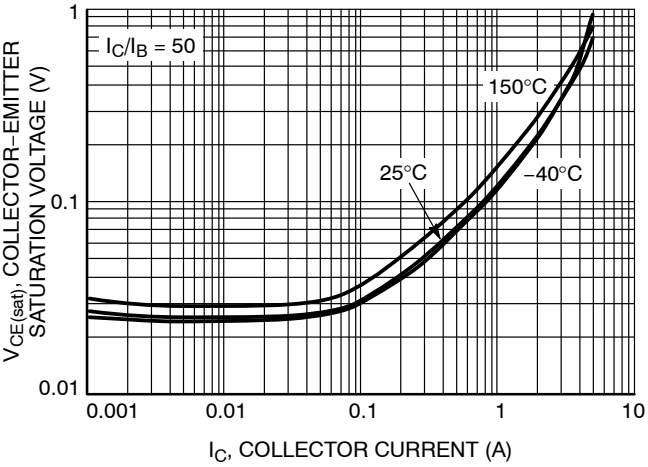


Figure 5. Collector−Emitter Saturation Voltage

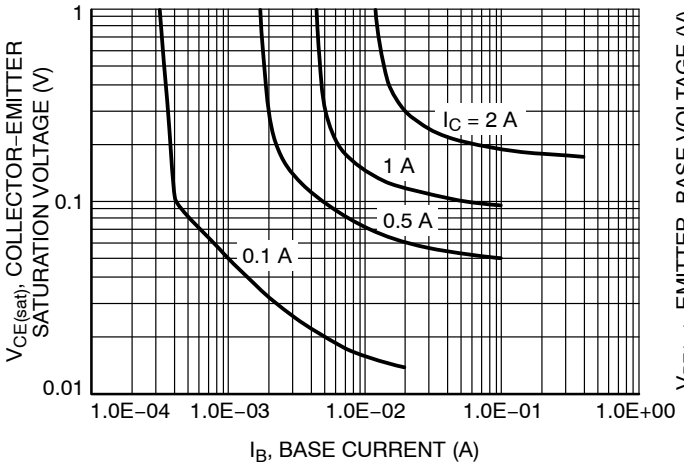


Figure 6. Collector Saturation Region

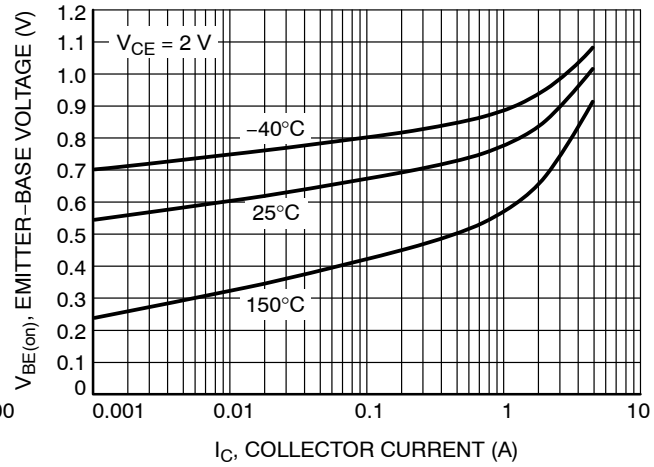


Figure 7. $V_{BE(on)}$ Voltage

TYPICAL CHARACTERISTICS

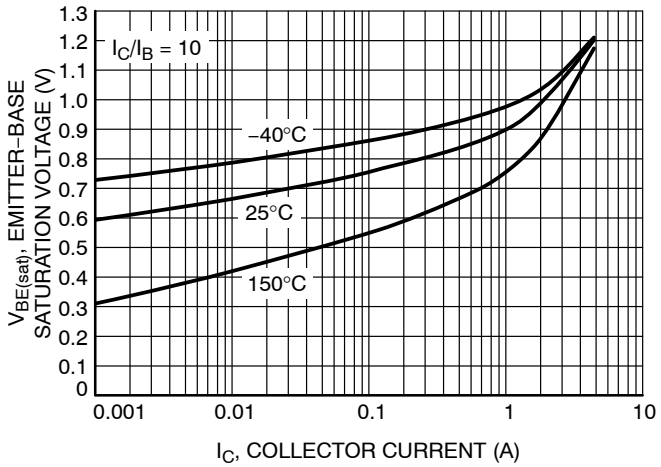


Figure 8. Base−Emitter Saturation Voltage

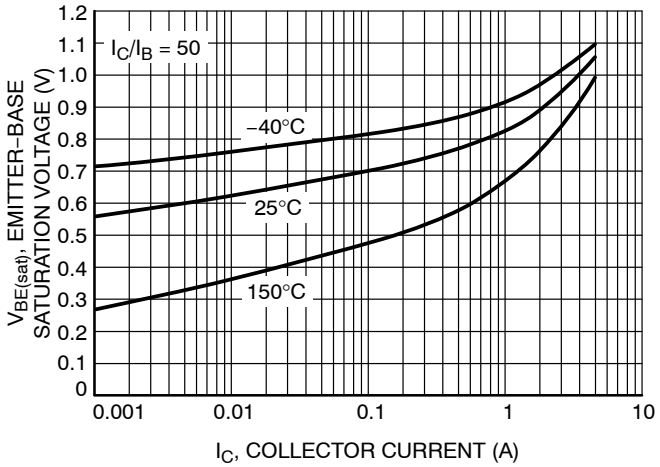


Figure 9. Base−Emitter Saturation Voltage

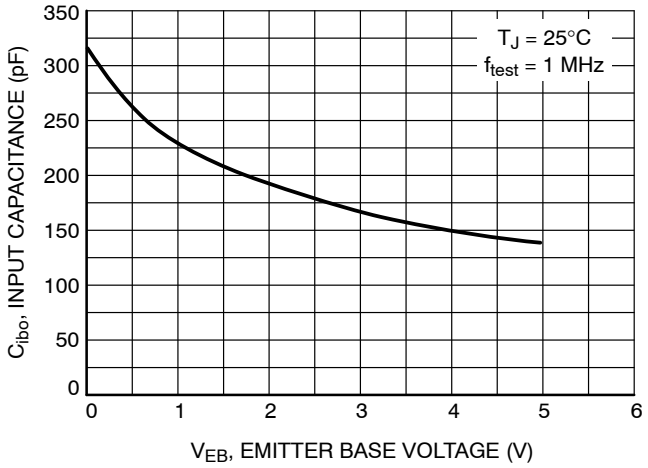


Figure 10. Input Capacitance

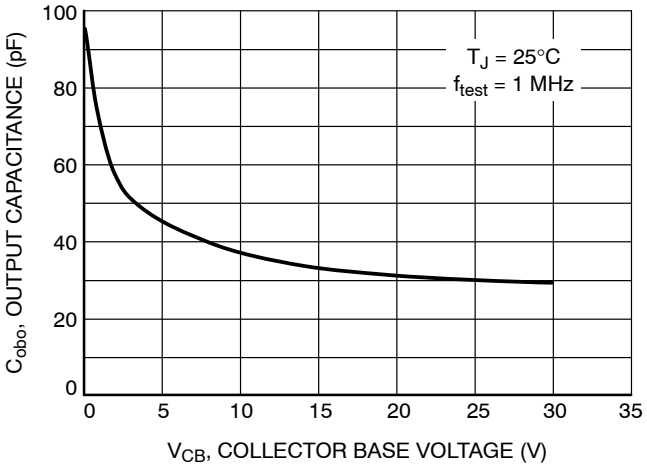


Figure 11. Output Capacitance

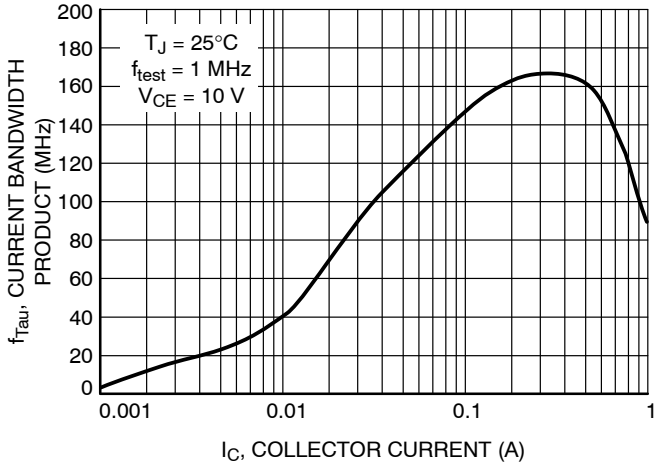


Figure 12. Current−Gain Bandwidth Product

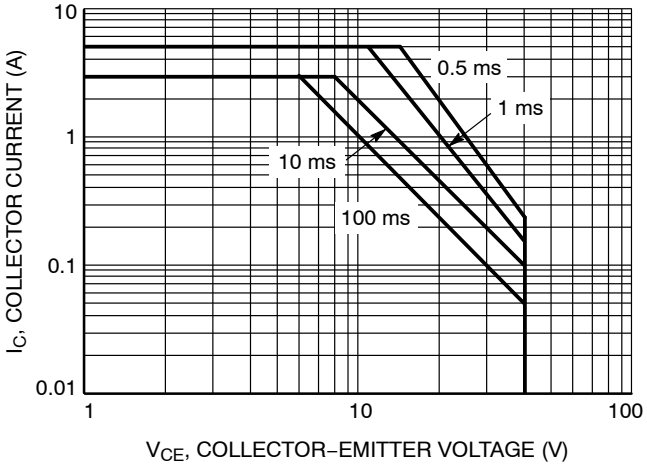
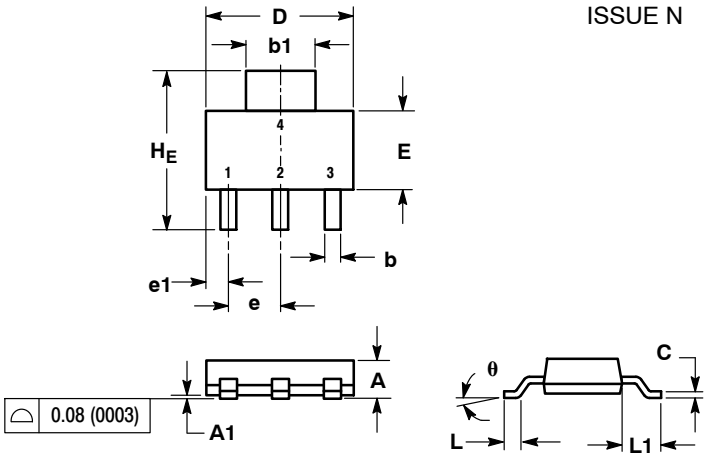


Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SOT−223 (TO−261)
CASE 318E−04
ISSUE N

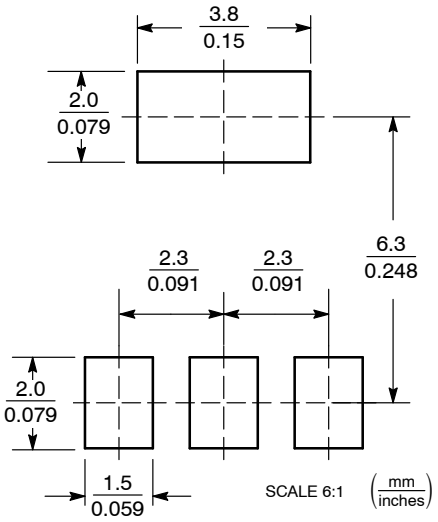


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	−−−	−−−	0.008	−−−	−−−
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	–	10°	0°	–	10°

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

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